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Amendments to the Claims

- 1. (previously presented) A method for manufacturing a light emitting diode having a transparent substrate, the method comprising:
 - forming a semiconductor multilayer on a first substrate producing a first multilayer structure;
 - forming a conductive amorphous interface layer on a second substrate, the second substrate being transparent in nature, producing a second multilayer structure;
 - bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure; and
- removing the first substrate from the third multilayer structure.
 - 2. (original) The method of claim 1 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.
- 3. (previously presented) The method of claim 1, wherein the amorphous interface layer is made of at least one selected from a group consisting of indium tin oxide, indium cadmium oxide, antimony tin oxide, and transparent adhesive agent.
- 4. (previously presented) A method for manufacturing a light emitting diode, comprising:
 - forming a semiconductor multilayer on a first substrate producing a first multilayer structure;
 - forming a conductive amorphous interface layer on a second substrate, the second substrate being transparent in nature, producing a second multilayer structure:
 - bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure; and
 - removing the first substrate from the third multilayer structure.

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- 5. (original) The method of claim 4 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.
- 6. (previously presented) The method of claim 4, wherein the amorphous interface layer
 is made of at least one selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, and transparent adhesive agent.
 - 7. (new) The method of claim 1 further comprising etching away a portion of the first multilayer structure to partially expose the amorphous interface layer.